XN01110 (XN1110)

Silicon PNP epitaxial planer transistor

For switching/digital circuits

Features

- Two elements incorporated into one package. (Emitter-coupled transistors with built-in resistor)
- Reduction of the mounting area and assembly cost by one half. •

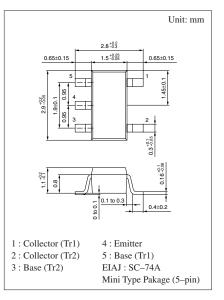
Basic Part Number of Element

• UNR1110(UN1110) × 2 elements

Parameter		Symbol	Ratings	Unit				
Rating of element	Collector to base voltage	V _{CBO}	-50	V				
	Collector to emitter voltage	V _{CEO}	-50	V				
	Collector current	I _C	-100	mA				
Overall	Total power dissipation	P _T	300	mW				
	Junction temperature	Tj	150	°C				
	Storage temperature	T _{stg}	-55 to +150	°C				

Absolute Maximum Ratings (Ta=25°C)

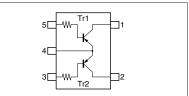
Electrical Characteristics (Ta=25°C)



Marking Symbol: AD

Internal Connection

min



typ

max

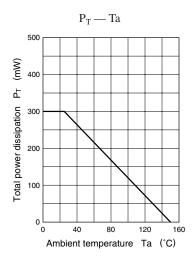
Conditions Parameter Symbol .14 **N**7 11 10.

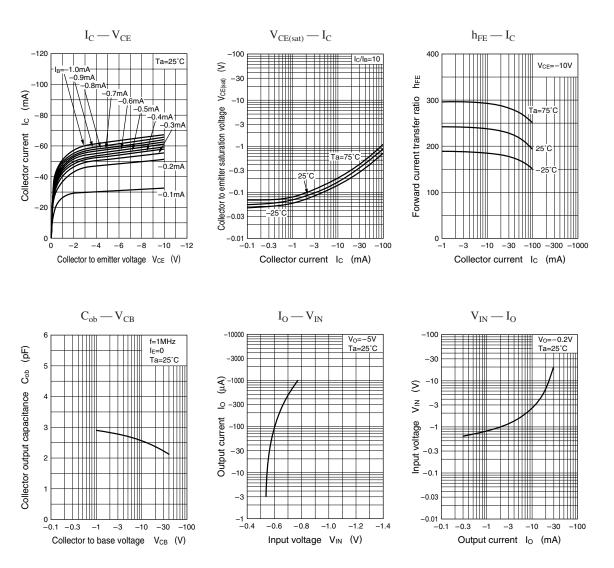
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Collector to base voltage	V	$I_{\rm C} = -10\mu A, I_{\rm F} = 0$	-50			V
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Collector to base voltage	V _{CBO}	$I_{\rm C} = -10\mu A, I_{\rm E} = 0$	-30			v
Collector cutoff currentCollCollCollCollCollColl I_{CEO} $V_{CE} = -50V, I_B = 0$ -0.5 μA Emitter cutoff current I_{EBO} $V_{EB} = -6V, I_C = 0$ -0.01 mAForward current transfer ratio h_{FE} $V_{CE} = -10V, I_C = -5mA$ 160460Forward current transfer h_{FE} ratio h_{FE} (small/large)*1 $V_{CE} = -10V, I_C = -5mA$ 0.50.99	Collector to emitter voltage	V _{CEO}	$I_{C} = -2mA, I_{B} = 0$	-50			V
$\begin{tabular}{ c c c c c c } \hline I_{CEO} & V_{CE} = -50V, I_B = 0 & & -0.5 & \mu A \\ \hline Emitter cutoff current & I_{EBO} & V_{EB} = -6V, I_C = 0 & & -0.01 & m A \\ \hline Forward current transfer ratio & h_{FE} & V_{CE} = -10V, I_C = -5mA & 160 & 460 & \\ \hline Forward current transfer h_{FE} ratio & h_{FE} (small/large)^{*1} & V_{CE} = -10V, I_C = -5mA & 0.5 & 0.99 & \\ \hline \end{array}$	Callester autoff aurent	I _{CBO}	$V_{CB} = -50V, I_E = 0$			- 0.1	μΑ
Forward current transfer ratio h_{FE} $V_{CE} = -10V$, $I_C = -5mA$ 160460Forward current transfer h_{FE} ratio $h_{FE} (small/large)^{*1}$ $V_{CE} = -10V$, $I_C = -5mA$ 0.50.99		I _{CEO}	$V_{CE} = -50V, I_B = 0$			- 0.5	μΑ
Forward current transfer h_{FE} ratio $h_{FE} (small/large)^{*1}$ $V_{CE} = -10V, I_C = -5mA$ 0.50.99	Emitter cutoff current	I _{EBO}	$V_{EB} = -6V, I_C = 0$			- 0.01	mA
	Forward current transfer ratio	\mathbf{h}_{FE}	$V_{CE} = -10V, I_C = -5mA$	160		460	
Collector to emitter saturation voltage $V_{CE(sat)}$ $I_C = -10mA$, $I_B = -0.3mA$ -0.25 V	Forward current transfer \mathbf{h}_{FE} ratio	h _{FE} (small/large)*1	$V_{CE} = -10V, I_C = -5mA$	0.5	0.99		
	Collector to emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = -10 {\rm mA}, I_{\rm B} = -0.3 {\rm mA}$			- 0.25	V
Output voltage high level V_{OH} $V_{CC} = -5V, V_B = -0.5V, R_L = 1k\Omega$ -4.9 V	Output voltage high level	V _{OH}	$V_{CC} = -5V, V_B = -0.5V, R_L = 1k\Omega$	-4.9			V
Output voltage low level V_{OL} $V_{CC} = -5V, V_B = -2.5V, R_L = 1k\Omega$ -0.2 V	Output voltage low level	V _{OL}	V_{CC} = -5V, V_B = -2.5V, R_L = 1k Ω			- 0.2	V
Transition frequency f_T $V_{CB} = -10V$, $I_E = 1mA$, $f = 200MHz$ 80MHz	Transition frequency	f_T	$V_{CB} = -10V, I_E = 1mA, f = 200MHz$		80		MHz
Input resistance R_1 -30% 47 $+30\%$ $k\Omega$	Input resistance	R ₁		-30%	47	+30%	kΩ

*1 Ratio between 2 elements

Note.) The Part number in the Parenthesis shows conventional part number.

Unit





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